TOSHIBA 1DL41

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

SWITCHING TYPE POWER SUPPLY APPLICATIONS

Repetitive Peak Reverse Voltage $: V_{RRM} = 200 V$

 $: I_{F(AV)} = 1.0 \text{ A (Ta} = 64^{\circ}\text{C)}$ Average Forward Current

Very Fast Reverse-Recovery Time : $t_{rr} = 60 \text{ ns}$ (Max.)

Low Forward Voltage $: V_{FM} = 0.98 V \text{ (Max.)}$

Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	v_{RRM}	200	V
Average Forward Current (Ta = 64°C)	I _{F (AV)}	1.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	30 (50 Hz)	A
Junction Temperature	$T_{ m j}$	-40~150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~150	°C

1. ANODE CATHODE **JEDEC EIAJ TOSHIBA** 3-3E1A

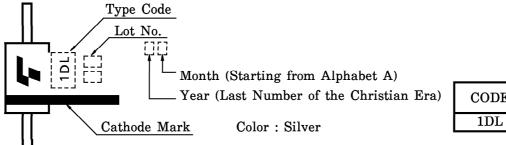
Unit in mm

Weight: 0.225 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{ extbf{FM}}$	$I_{\text{FM}} = 1.0 \text{ A}$	_	_	0.98	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 200 V$	_	_	100	μ A
Reverse Recovery Time	t_{rr}	$I_{\rm F} = 1 {\rm A}, {\rm di} / {\rm dt} = -20 {\rm A} / \mu {\rm s}$	_	_	60	ns
Forward Recovery Time	t_{fr}	$I_{\mathrm{F}} = 1.0 \mathrm{A}$	_	_	100	ns
Thermal Resistance	R _{th (j-a)}	Junction to Ambient	_	_	115	°C/W
Thermal Resistance	$R_{ ext{th }(j-\ell)}$	Junction to Lead	_	_	45	°C/W

MARKING

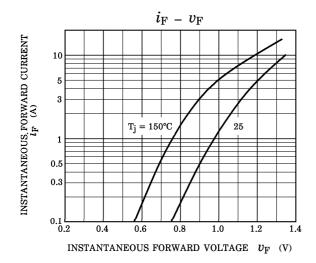


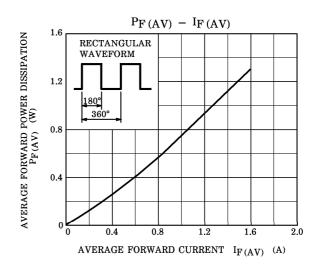
CODE	TYPE
1DL	1DL41

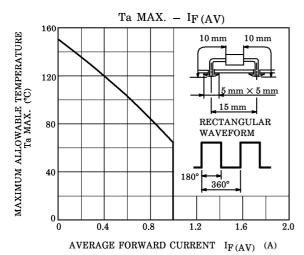
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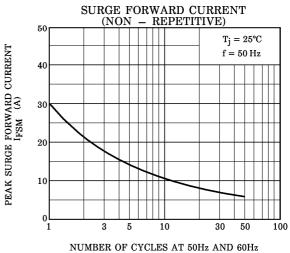
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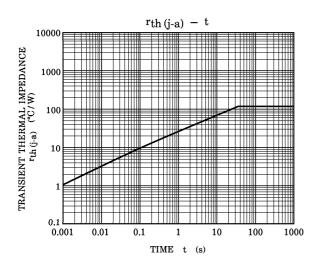
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